

AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

Listing of Claims:

1-29. (Cancelled)

30. (Previously Presented) An abrasive comprising cerium oxide particles, said particles having a crystal grain boundary and having a maximum diameter of not larger than 3000 nm.

31. (Previously Presented) An abrasive comprising cerium oxide particles, wherein a crystallite of said cerium oxide particles having a crystal grain boundaries has a maximum diameter not larger than 600 nm.

32. (Previously Presented) The abrasive of Claim 30, wherein said crystallite of said cerium oxide particles has a maximum diameter of not larger than 600 nm.

33. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles have pores.

34. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles have a porosity of from 10 to 30% as determined from the ratio of a true density measured with a pycnometer to a theoretical density determined by X-ray Rietvelt analysis.

35. (Currently Amended) The abrasive of Claim 30, wherein said cerium oxide particles have a pore volume of from $[[0.2]]\underline{0.02}$ to $0.05\text{cm}^3/\text{g}$ as measured by B.J.H. method.

36. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles have a bulk density not higher than 6.5 g/cm^3 .

37. (Previously Presented) The abrasive of Claim 30 further comprising a medium, wherein said medium is water.

38. (Previously Presented) The abrasive of Claim 30 further comprising a dispersant.

39. (Previously Presented) The abrasive of Claim 38, wherein said dispersant is at least one selected from a water-soluble organic polymer, a water-soluble anionic surfactant, a water-soluble nonionic surfactant and water-soluble amine.

40. (Previously Presented) An abrasive as claimed in claim 39 wherein said dispersant is a polyacrylic acid type polymer.

41. (Previously Presented) The abrasive of Claim 30 wherein cerium oxide particles with a diameter not smaller than $1\mu\text{m}$ occupies at least 0.1% by weight of the total weight of the cerium oxide particles.

42. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles having said crystal grain boundary have a property of polishing a target member while collapsing.

43. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles having said crystal grain boundary have a property of polishing a target member while forming new surfaces not coming into contact with said medium.

44. (Previously Presented) The abrasive of Claim 30, wherein a content of the cerium oxide particles having a particle diameter not smaller than $0.5\mu\text{m}$ after polishing, measured by centrifugal sedimentation after polishing a predetermined target substrate, is in a ratio of not more than 0.8 with respect to that content before polishing.

45. (Currently Amended) The abrasive of Claim 30, wherein cerium oxide particle diameter at D90% by volume measured by laser diffraction after a target substrate has been polished is in

a ratio of from 0.4 to ~~[[09]]~~0.9 with respect to that particle diameter before polishing.

46. (Currently Amended) A method of polishing a predetermined substrate, comprising polishing said substrate using an abrasive as claimed in 30 comprising cerium oxide particles, said particles having a crystal grain boundary and having a maximum diameter of not larger than 3000 nm.

47. (Currently Amended) A method of polishing a substrate as claimed in claim 46, wherein strength of the substrate is larger than the breaking strength of grain boundary of ~~an oxidation~~the cerium oxide particles.

48. (Previously Presented) The method of polishing the substrate as claimed in claim 46 wherein said predetermined substrate is a semiconductor chip with a silica film formed thereon.

49. (Currently Amended) A manufacturing method of a semiconductor device comprising the step of polishing a semiconductor chip having a silica film formed thereon with an abrasive ~~as claimed in claim 30~~ comprising cerium oxide particles, said particles having a crystal grain boundary and having a maximum diameter of not larger than 3000 nm.